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Information Disclosure Statement Form PTO-1449 and Cited Reference(s)

January 21, 2004 YOR920030175US1 1500-419 (MJC)



LIST OF PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT Applicant(s): Allen et al.

YOR920030175US1

Docket No.: YOR920030 Serial No.: 10/661,041

Filing Date: September 12, 2003

Group: 2811

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EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	FILING DATE  IF APPROPRIATE
	6,316,167	11/13/01	Angelopoulos et al.	430/313	
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	Proc. SPIE, Vol. Chung et al., "A Vol. 3999, pgs. DellaGuardia et SPIE, Vol. 4346 Lucas et al., "19 pgs. 725-736 (20	. 3999, pgs. 620 . Novel Resist N 305-312 (2000) al., "193 Litho , pgs. 1029-104 3 nm Contact F	Material for sub-100 nm Conta ). graphy and RELACS <sup>TM</sup> Proces 40 (2001). Thotoresist Reflow Feasibility S	ct Hole Pattern," Proc. SI ssing for BEOL Lithograp Study," Proc. SPIE, Vol.	PIE, hy," Proc. 4345,
	Satou et al., "Su Lithography," Jp	b-0.10 µm Hole n. J. Appl. Phy	Fabrication Using Bilayer Sil s. 1, Vol. 38, Part 1, No. 12B,	lylation Process for 193 n pgs 7008-7012 (Decembe	m er 1999).
xaminer				Date Considered	1

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

Page 1 of 1

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LIST OF PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT Applicant(s): Allen et al.

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4	Chun et al., "Co	ontact Hole Size	e Reducing Methods by Using	Water-Soluble Organic C	yer-Coating
	Material (WAS	OOM) as a Bar	rier Layer Toward 0.15 um Cor	ntact Hole; Resist Flow T	echnique I,"
	Proc. SPIE, Vo.	1. 3999, pgs. 62	0-626 (2000).		
a/	Changet of #A	Novel Design	Material for sub-100 nm Conta	et Wole Dettern " Drog Si	D <b>TE</b>
4		305-312 (2000		ici noie Fatterii, Froc. Si	rue,
	, or, 2222, bear	,303 312 (2000	<b>)</b>		
<u>C</u>			graphy and RELACSTM Proces	ssing for BBOL Lithograp	hy," Proc.
	SPIE, Vol. 4340	6, pgs. 1029-10	40 (2001). ·		
. /	Tuesdat al #10	32 mm Cantast !	Photoresist Reflow Feasibility S	C6.d" D=00 CDTC 3741	1215
	pgs. 725-736 (2	55 mm Contact 1 2001).	motoresist Keliuw reasibility	Sivuy, Proc. Spie, Vol.	43 <b>4</b> 3,
	/ Page 120 130 (2	100 k j.			
0	Satou et al., "Su	ıb-0.10 μm Hol	e Fabrication Using Bilayer Sil	lylation Process for 193 n	m
•	Lithography," J	pn. J. Appl. Phy	/s. 1, Vol. 38, Part 1, No. 12B,	pgs 7008-7012 (Decemb	er 1999).

Examiner

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Information Disclosure Statement Form PTO-1449 and Cited Reference(s)



February 23, 2005 YOR920030175US1 1500-419 (MJC)

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LIST OF PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT Applicant(s): Allen et al.

Docket No.:

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Group: 2811

		Ţ	J.S. PATENT DOCUMENTS		<u> </u>
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	filing date <u>if appropriati</u>
	5,753,418	05/19/98	Tsai et al.	430/313	
	6,009,888	01/04/00	Ye et al.	134/1.3	
	6,316,167	11/13/01	Angelopoulos et al.	430/313	
	6,387,798	05/14/02	Loke et al.	438/623	
	6,514,867	02/04/03	Hui et al.	438/713	
		FOR	EIGN PATENT DOCUMENTS		
EXAMINER NITIAL	DOCUMENT NO.	DATE	COUNTRY	CLASS/SUBCLASS	TRANSLATION YES NO
	EP 0 236 220 A1	13/04/88	Europe		
			OTHER DOCUMENTS		
XAMINER NITIAL	REF NO. AUTHOR	r, title, date, pe	RTINENT PAGES, ETC.	<b></b>	
	American Vacuum Mahorowala et al.	n Society, Pg , "Tunable A	ization for Tapered Contact Etch," s. 1845-1851 (Sept/Oct 2001). .nti-Reflective Coatings with Built- sing," Proceedings of the SPIE, Vo	In Hard Mask Prope	rties

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Car_	6,009,888	01/04/00	Ye et al.	134/1.3	
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		FOR	EIGN PATENT DOCUMENTS	-	
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	American Vacuum Mahorowala et al.	n Society, Pg , "Tunable A	ization for Tapered Contact Etch," J. s. 1845-1851 (Sept/Oct 2001)nti-Reflective Coatings with Built-In sing," Proceedings of the SPIE, Vol. 4	Hard Mask Proper	nties

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